



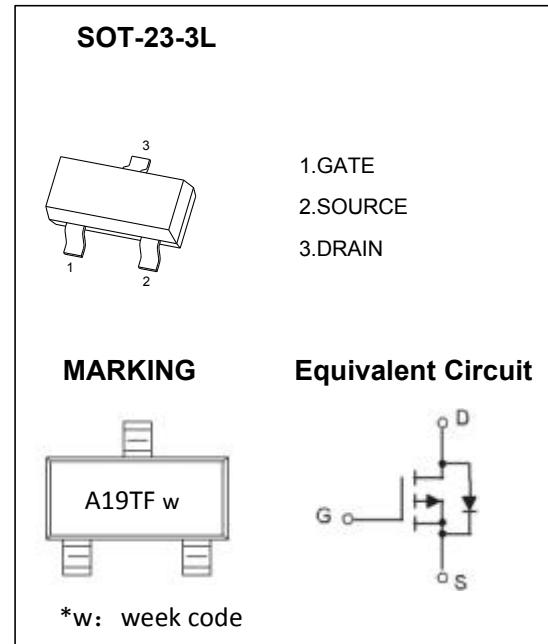
SHENZHEN TUOFENG SEMICONDUCTOR TECHNOLOGY CO.,LTD

# SOT-23-3L Plastic-Encapsulate MOSFETS

TF3401

## TF3401 P-Channel 30-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	$I_D$
-30V	0.053Ω@-10V	-4.2A
	0.065Ω@-4.5V	
	0.085Ω@-2.5V	



### General FEATURE

- TrenchFET Power MOSFET
- Lead free product is acquired
- Surface mount package

### APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

### Maximum ratings ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	±12	
Continuous Drain Current	$I_D$	-4.2	A
Pulsed Drain Current	$I_{DM}$	-30	
Maximum Power Dissipation	$P_D$	1.25	W
Thermal Resistance from Junction to Ambient( $t \leq 5\text{s}$ )	$R_{\theta JA}$	95	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 ~+150	



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## MOSFET ELECTRICAL CHARACTERISTICS

T<sub>a</sub> = 25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static characteristics</b>						
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V			-1	μA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V			±100	nA
Drain-source on-resistance (note a)	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.0A		50	53	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A		60	65	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.5A		80	85	mΩ
Forward transconductance (note a)	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4.2A	7	10		S
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.6	-1	-1.2	V
Diode forward voltage (note a)	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V			-1.2	V
<b>Dynamic characteristics (note b)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		950		pF
Output capacitance	C <sub>oss</sub>			115		pF
Reverse transfer capacitance	C <sub>rss</sub>			75		pF
<b>Switching Characteristics (note b)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -4.2A, R <sub>GEN</sub> = 6Ω		7.0		ns
Turn-on rise time	t <sub>r</sub>			3.0		ns
Turn-off delay time	t <sub>d(off)</sub>			30		ns
Turn-off fall time	t <sub>f</sub>			12		ns

### Notes:

a. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤ 2%.

b. These parameters have no way to verify.

## Typical Electrical and Thermal Characteristics

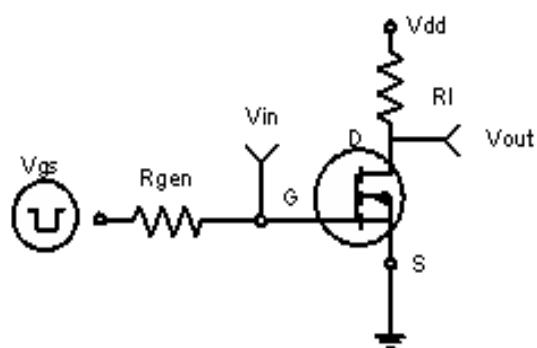


Figure 1:Switching Test Circuit

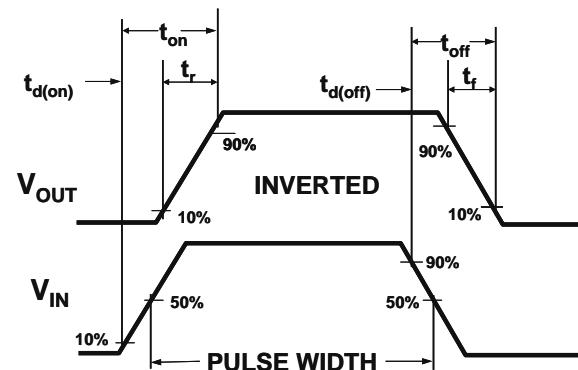
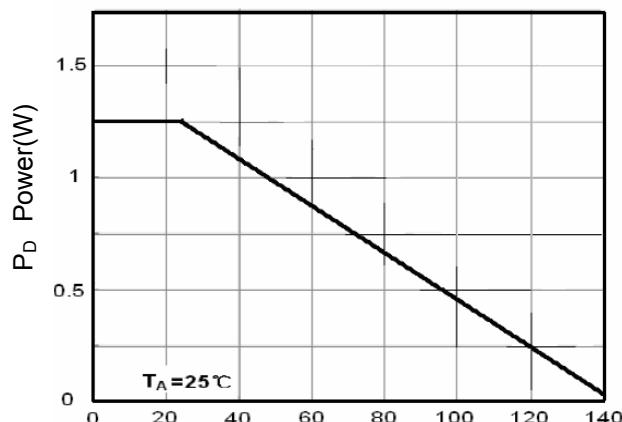
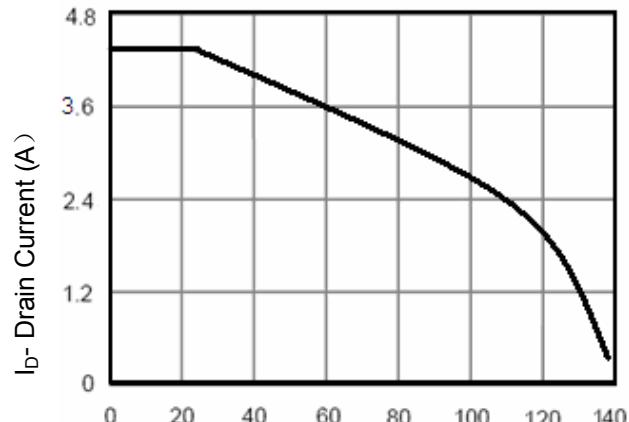


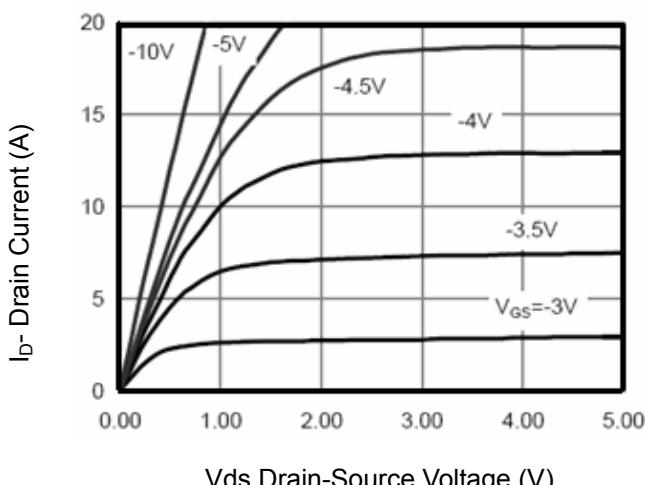
Figure 2:Switching Waveforms



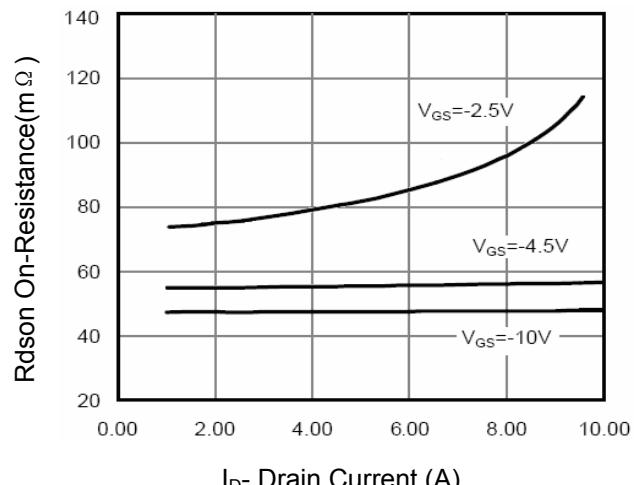
T<sub>J</sub>-Junction Temperature(°C)  
Figure 3 Power Dissipation



T<sub>J</sub>-Junction Temperature(°C)  
Figure 4 Drain Current



V<sub>DS</sub> Drain-Source Voltage (V)  
Figure 5 Output Characteristics



I<sub>D</sub>- Drain Current (A)  
Figure 6 Drain-Source On-Resistance

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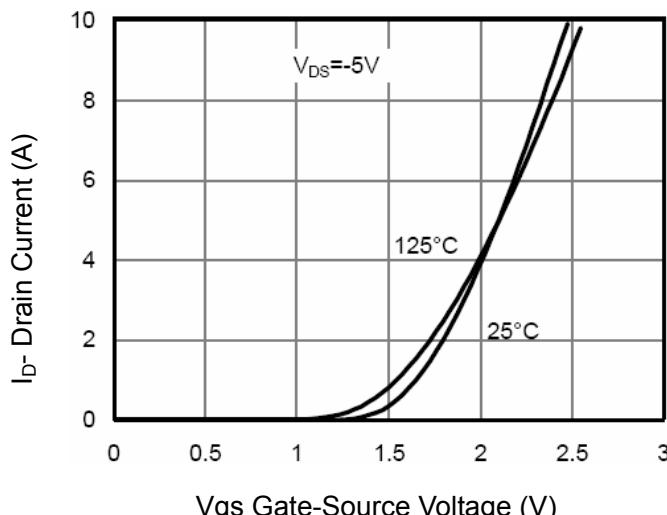


Figure 7 Transfer Characteristics

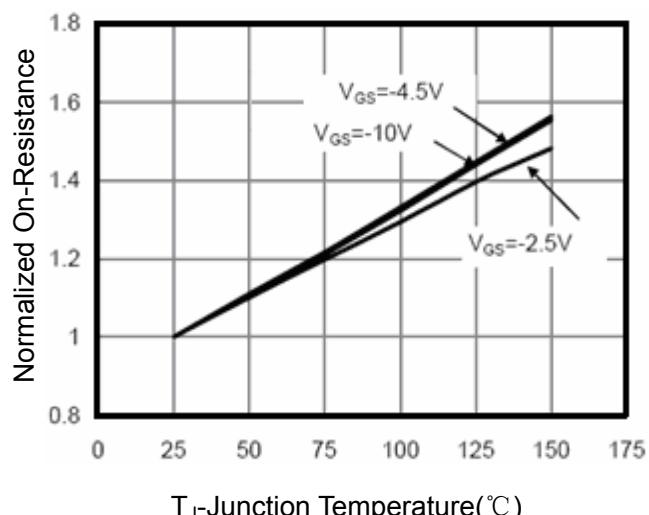


Figure 8 Drain-Source On-Resistance

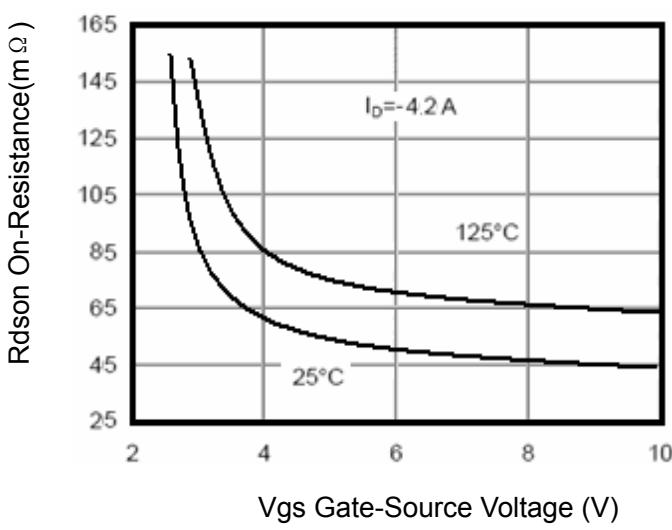


Figure 9  $R_{DSON}$  vs  $V_{GS}$

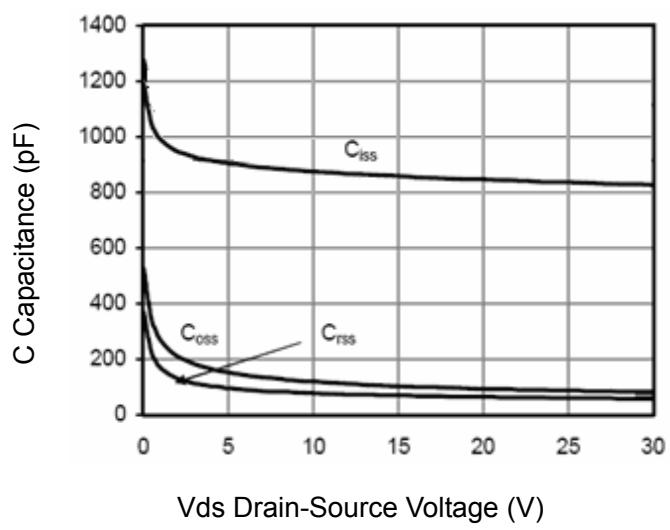


Figure 10 Capacitance vs  $V_{DS}$

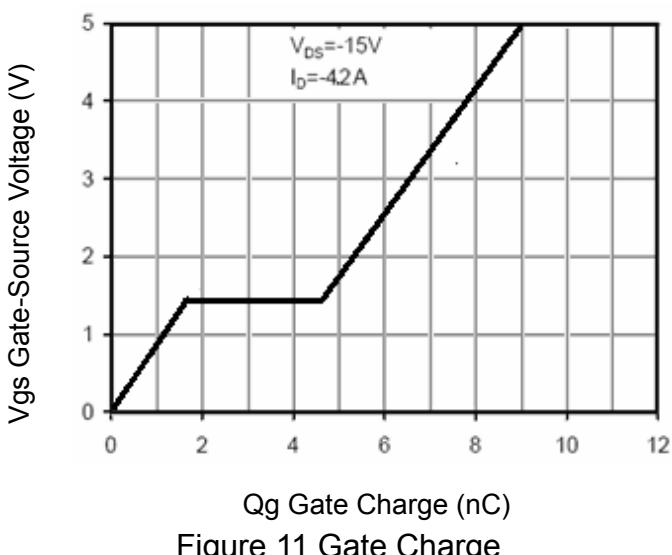


Figure 11 Gate Charge

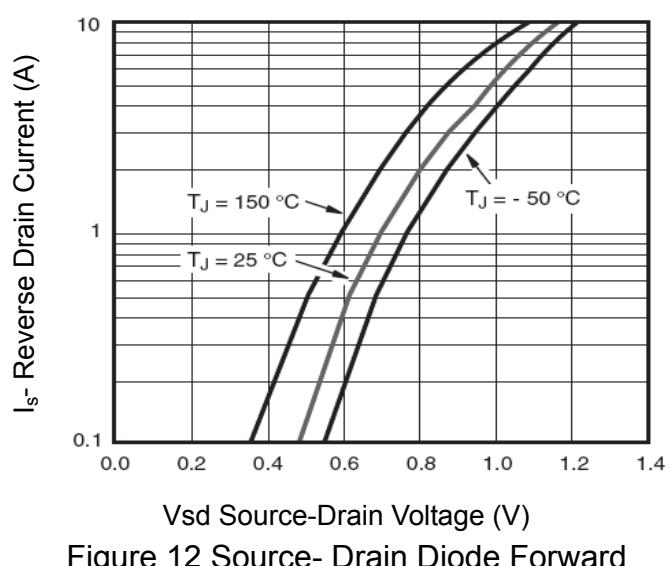


Figure 12 Source- Drain Diode Forward

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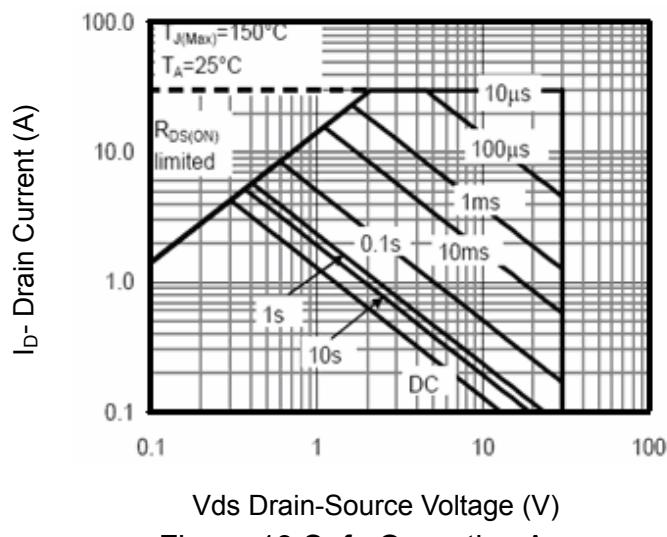


Figure 13 Safe Operation Area

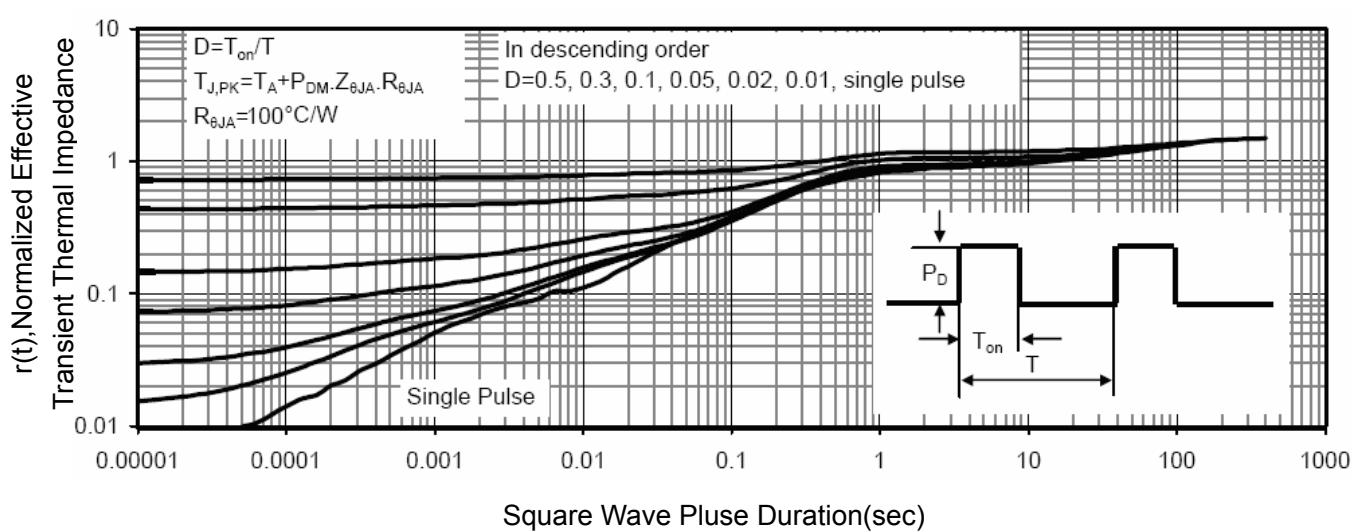


Figure 14 Normalized Maximum Transient Thermal Impedance

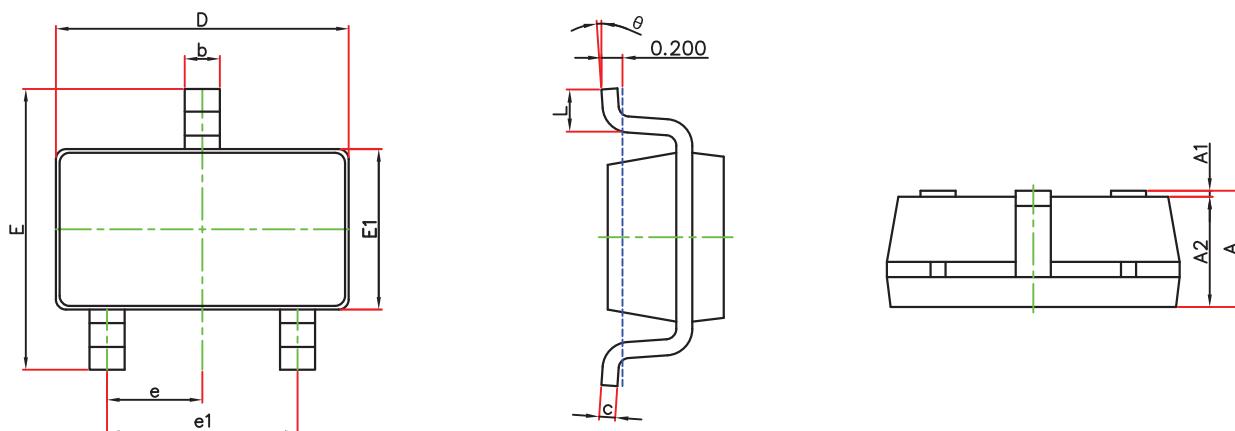


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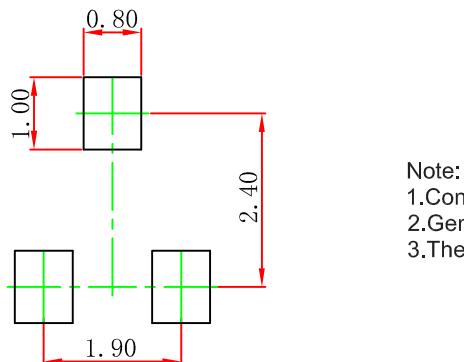
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## SOT-23-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

## SOT-23-3L Suggested Pad Layout



### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

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